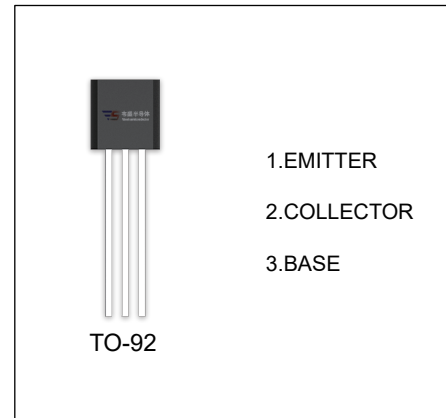


MPS751 TRANSISTOR (PNP)

● FEATURES

Switching and Amplifier Applications



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
MPS751	TO-92	Bulk	1000pcs/Bag
MPS751-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-2	A
P_C	Collector Dissipation	0.625	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	200	$^{\circ}\text{C/W}$
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

$T_a=25\text{ }^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}, I_E=0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}^*$	$I_C=-10\text{mA}, I_B=0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-80\text{V}, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4\text{V}, I_C=0$			-0.1	μA
DC current gain	$h_{FE(1)}^*$	$V_{CE}=-2\text{V}, I_C=-50\text{mA}$	75			
	$h_{FE(2)}^*$	$V_{CE}=-2\text{V}, I_C=-500\text{mA}$	75			
	$h_{FE(3)}^*$	$V_{CE}=-2\text{V}, I_C=-1\text{A}$	75			
	$h_{FE(4)}^*$	$V_{CE}=-2\text{V}, I_C=-2\text{A}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}^*$	$I_C=-2\text{A}, I_B=-200\text{mA}$			-0.5	V
		$I_C=-1\text{A}, I_B=-100\text{mA}$			-0.3	
Base -emitter saturation voltage	$V_{BE(sat)}^*$	$I_C=-1\text{A}, I_B=-100\text{mA}$			-1.2	V
Base -emitter on voltage	$V_{BE(on)}^*$	$V_{CE}=-2\text{V}, I_C=-1\text{A}$			-1	V
Transition frequency	f_T	$V_{CE}=-5\text{V}, I_C=-50\text{mA}, f=100\text{MHz}$	75			MHz

 * Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle = 2.0%.

